

# IGBT – Power, Co-PAK N-Channel, Field Stop VII (FS7), TO247-4L 1200 V, 1.7 V, 75 A

## FGY4L75T120SWD

### Description

Using the novel field stop 7th generation IGBT technology and the Gen7 Diode in TO247 4-lead package, FGY4L75T120SWD offers the optimum performance with low switching and conduction losses for high-efficiency operations in various applications like Solar Inverter, UPS and ESS.

### Features

- Maximum Junction Temperature  $T_J = 175^{\circ}\text{C}$
- Positive Temperature Coefficient for Easy Parallel Operation
- High Current Capability
- Smooth and Optimized Switching
- Low Switching Loss
- RoHS Compliant

### Applications

- Solar Inverter
- UPS
- Energy Storage System

### MAXIMUM RATINGS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

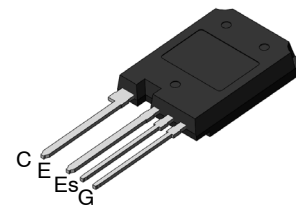
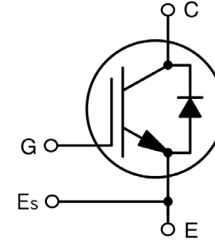
Parameter	Symbol	Value	Unit
Collector-to-Emitter Voltage	$V_{CE}$	1200	V
Gate-to-Emitter Voltage	$V_{GE}$	$\pm 20$	
Transient Gate-to-Emitter Voltage		$\pm 30$	
Collector Current	$T_C = 25^{\circ}\text{C}$ (Note 1)	$I_C$	A
		150	
Power Dissipation	$T_C = 25^{\circ}\text{C}$	$P_D$	W
		652	
Pulsed Collector Current	$T_C = 25^{\circ}\text{C}$ , $t_p = 10 \mu\text{s}$ (Note 2)	$I_{CM}$	A
		300	
Diode Forward Current	$T_C = 25^{\circ}\text{C}$ (Note 1)	$I_F$	A
		150	
Pulsed Diode Forward Current	$T_C = 25^{\circ}\text{C}$ , $t_p = 10 \mu\text{s}$ (Note 2)	$I_{FM}$	A
		300	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	$-55$ to $+175$	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes	$T_L$	265	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limited by bond wire
2. Repetitive rating: Pulse width limited by max. junction temperature.

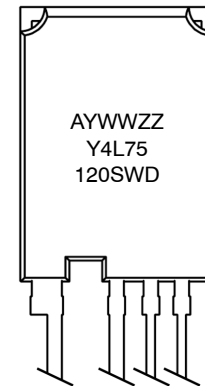
$BV_{CES}$	$V_{CE(SAT\_TYP)}$	$I_C$
1200 V	1.7 V	75 A

### PIN CONNECTIONS



TO-247-4LD  
CASE 340BW

### MARKING DIAGRAM



A = Assembly Location  
 YWW = Date code (Year & week)  
 ZZ = Assembly Lot  
 Y4L75120SWD = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping
FGY4L75T120SWD	TO-247-4LD (Pb-Free)	30 Units / Tube

# FGY4L75T120SWD

## THERMAL CHARACTERISTICS

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Thermal Resistance, Junction-to-Case for IGBT	$R_{\theta JC}$	–	0.18	0.23	°C/W
Thermal Resistance, Junction-to-Case for Diode	$R_{\theta JCD}$	–	0.3	0.39	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	–	–	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-to-Emitter Breakdown Voltage	$BV_{CES}$	$V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$	1200	–	–	V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{CES}}{\Delta T_J}$	$V_{GE} = 0\text{ V}, I_C = 9.99\text{ mA}$	–	1120	–	mV/°C
Collector-to-Emitter Cut-Off Current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	–	–	40	μA
Gate-to-Emitter Leakage Current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}, V_{CE} = 0\text{ V}$	–	–	±400	nA

### ON CHARACTERISTICS

Gate-to-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	5.6	6.5	7.4	V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 25^\circ\text{C}$	–	1.7	2.0	
		$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 175^\circ\text{C}$	–	2.4	–	

### DYNAMIC CHARACTERISTICS

Input Capacitance	$C_{ies}$	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	–	7190	–	pF
Output Capacitance	$C_{oes}$		–	222	–	
Reverse Transfer Capacitance	$C_{res}$		–	30.1	–	
Total Gate Charge	$Q_g$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 75\text{ A}$	–	225.6	–	nC
Gate-to-Emitter Charge	$Q_{ge}$		–	66.4	–	
Gate-to-Collector Charge	$Q_{gc}$		–	84.8	–	

### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 37.5\text{ A}, R_G = 11.5\ \Omega, T_J = 25^\circ\text{C}$	–	62.8	–	ns
Rise Time	$t_r$		–	20.8	–	
Turn-off Delay Time	$t_{d(off)}$		–	273.6	–	
Fall Time	$t_f$		–	74	–	
Turn-on Switching Loss	$E_{on}$		–	1.6	–	mJ
Turn-off Switching Loss	$E_{off}$		–	1.2	–	
Total Switching Loss	$E_{ts}$		–	2.8	–	
Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}, I_C = 75\text{ A}, R_G = 11.5\ \Omega, T_J = 25^\circ\text{C}$	–	65.6	–	ns
Rise Time	$t_r$		–	28.8	–	
Turn-off Delay Time	$t_{d(off)}$		–	241.6	–	
Fall Time	$t_f$		–	62.4	–	
Turn-on Switching Loss	$E_{on}$		–	2.9	–	mJ
Turn-off Switching Loss	$E_{off}$		–	2.1	–	
Total Switching Loss	$E_{ts}$		–	5.0	–	

# FGY4L75T120SWD

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 37.5\text{ A}, R_G = 11.5\ \Omega, T_J = 175^\circ\text{C}$	–	51.2	–	ns
Rise Time	$t_r$		–	24.0	–	
Turn-off Delay Time	$t_{d(off)}$		–	323.2	–	
Fall Time	$t_f$		–	126.4	–	
Turn-on Switching Loss	$E_{on}$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, R_G = 11.5\ \Omega, T_J = 175^\circ\text{C}$	–	3.1	–	mJ
Turn-off Switching Loss	$E_{off}$		–	1.8	–	
Total Switching Loss	$E_{ts}$		–	4.9	–	
Turn-on Delay Time	$t_{d(on)}$		–	57.2	–	ns
Rise Time	$t_r$		–	35.2	–	
Turn-off Delay Time	$t_{d(off)}$		–	280	–	
Fall Time	$t_f$		–	104	–	
Turn-on Switching Loss	$E_{on}$	$V_{CE} = 600\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 75\text{ A}, R_G = 11.5\ \Omega, T_J = 175^\circ\text{C}$	–	5.2	–	mJ
Turn-off Switching Loss	$E_{off}$		–	2.8	–	
Total Switching Loss	$E_{ts}$		–	8.1	–	

### DIODE CHARACTERISTICS

Forward Voltage	$V_F$	$I_F = 75\text{ A}, T_J = 25^\circ\text{C}$	1.74	2.04	2.34	V
		$I_F = 75\text{ A}, T_J = 175^\circ\text{C}$	–	2.2	–	

### DIODE SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 37.5\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$	–	145.3	–	ns
Reverse Recovery Charge	$Q_{rr}$		–	2.56	–	$\mu\text{C}$
Reverse Recovery Energy	$E_{REC}$		–	0.77	–	mJ
Peak Reverse Recovery Current	$I_{RRM}$		–	35.2	–	A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 75\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 25^\circ\text{C}$	–	208	–	ns
Reverse Recovery Charge	$Q_{rr}$		–	4.22	–	$\mu\text{C}$
Reverse Recovery Energy	$E_{REC}$		–	1.32	–	mJ
Peak Reverse Recovery Current	$I_{RRM}$		–	40.6	–	A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 37.5\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$	–	221.7	–	ns
Reverse Recovery Charge	$Q_{rr}$		–	5.54	–	$\mu\text{C}$
Reverse Recovery Energy	$E_{REC}$		–	1.85	–	mJ
Peak Reverse Recovery Current	$I_{RRM}$		–	48.7	–	A
Reverse Recovery Time	$t_{rr}$	$V_R = 600\text{ V}, I_F = 75\text{ A},$ $di_F/dt = 1000\text{ A}/\mu\text{s}, T_J = 175^\circ\text{C}$	–	307.1	–	ns
Reverse Recovery Charge	$Q_{rr}$		–	9.15	–	$\mu\text{C}$
Reverse Recovery Energy	$E_{REC}$		–	2.95	–	mJ
Peak Reverse Recovery Current	$I_{RRM}$		–	59.5	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# FGY4L75T120SWD

## TYPICAL CHARACTERISTICS

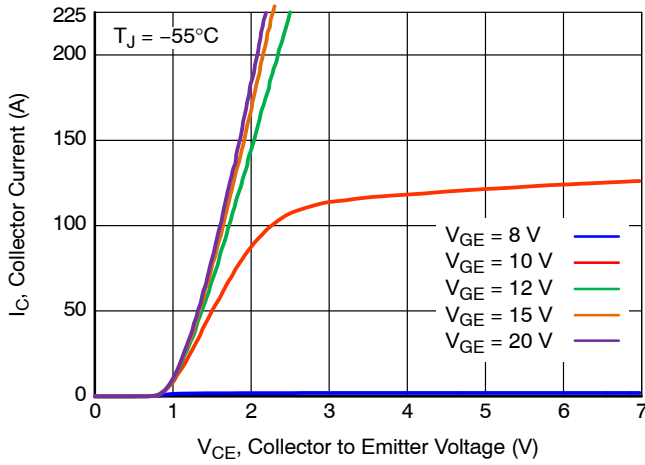


Figure 1. Output Characteristics

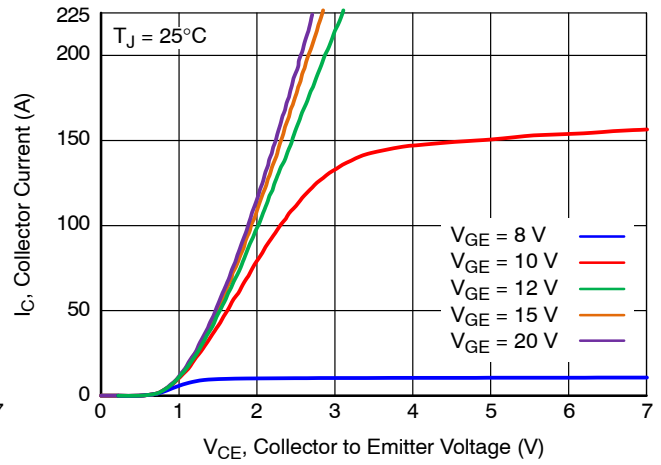


Figure 2. Output Characteristics

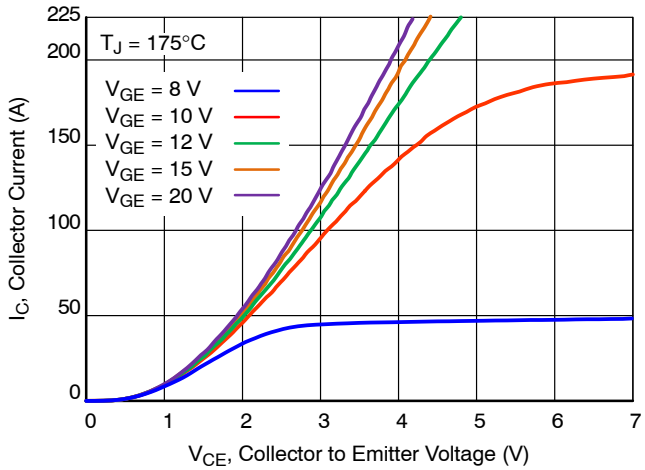


Figure 3. Output Characteristics

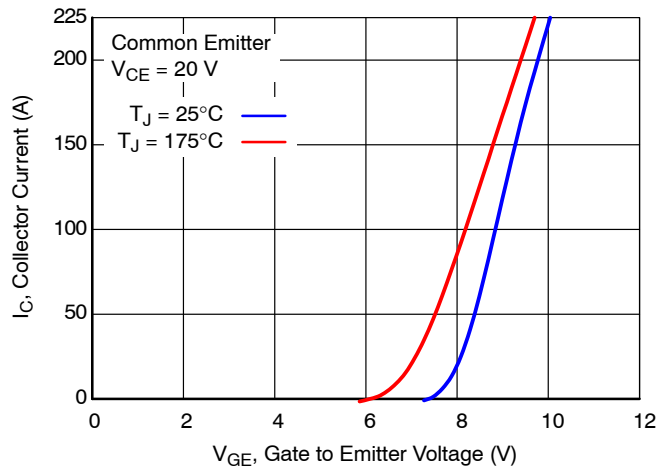


Figure 4. Transfer Characteristics

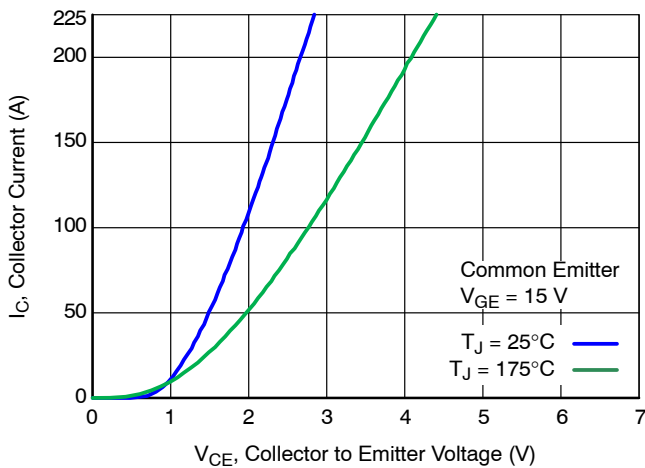


Figure 5. Saturation Characteristics

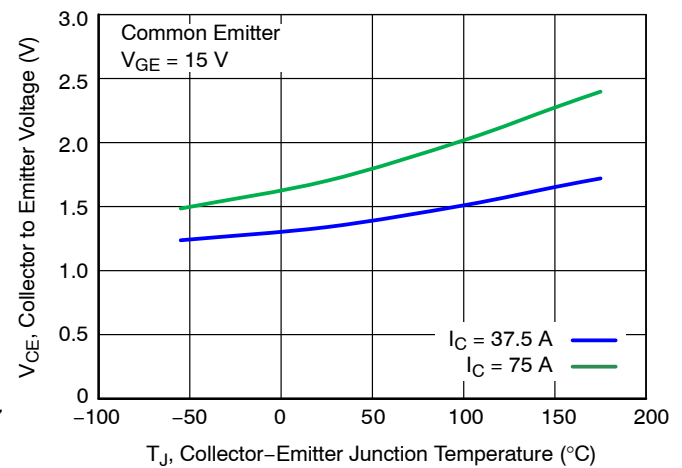


Figure 6. Saturation Voltage vs. Junction Temperature

TYPICAL CHARACTERISTICS

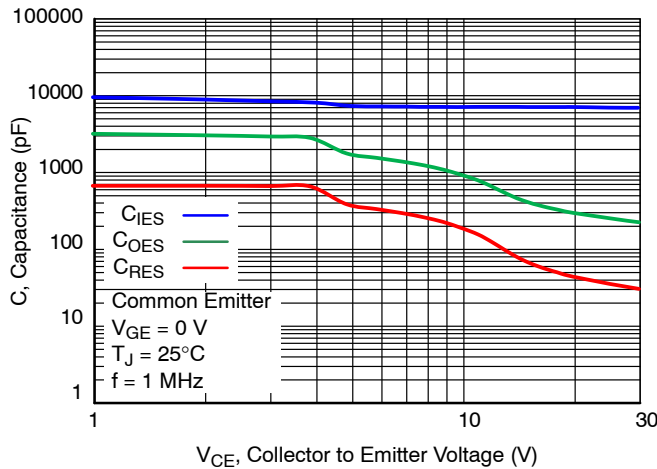


Figure 7. Capacitance Characteristics

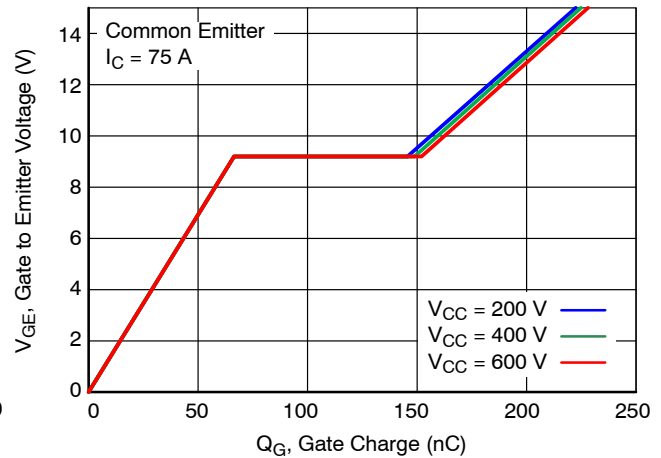


Figure 8. Gate Charge Characteristics

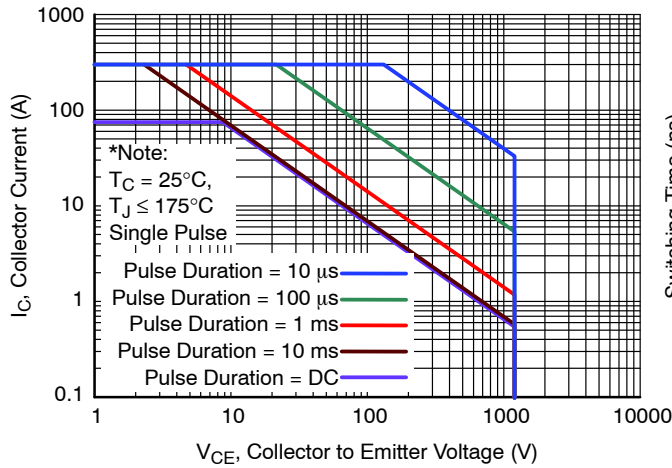


Figure 9. SOA Characteristics

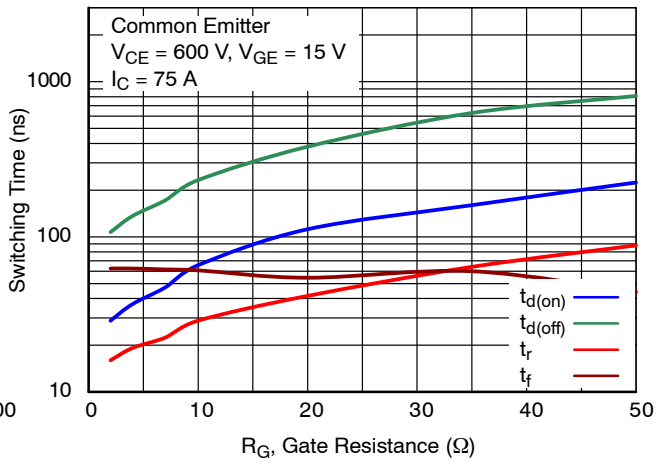


Figure 10. Switching Time vs. Gate Resistance ( $T_J = 25^\circ\text{C}$ )

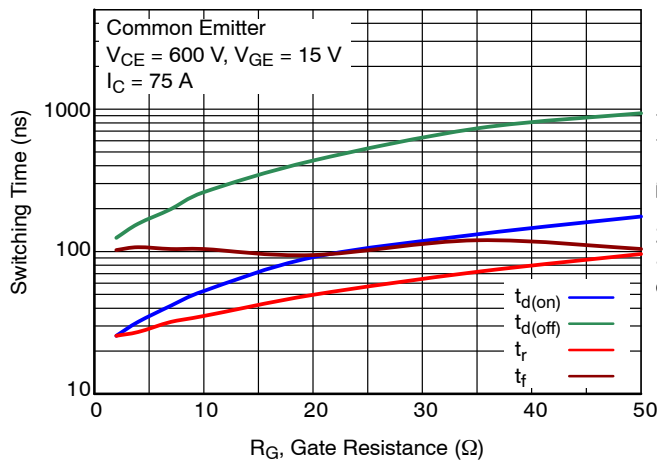


Figure 11. Switching Time vs. Gate Resistance ( $T_J = 175^\circ\text{C}$ )

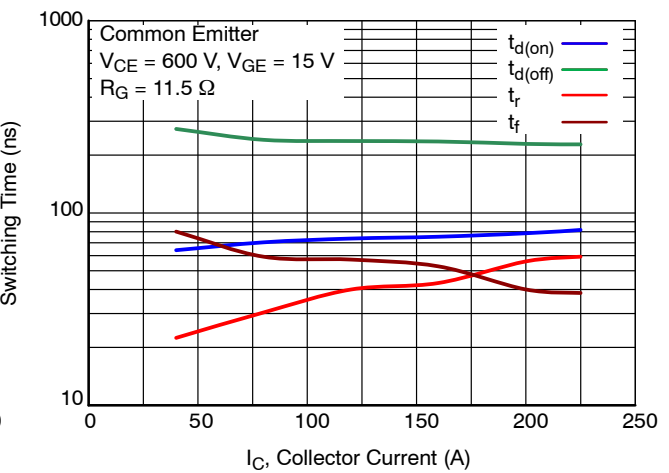


Figure 12. Switching Time vs. Collector Current ( $T_J = 25^\circ\text{C}$ )

TYPICAL CHARACTERISTICS

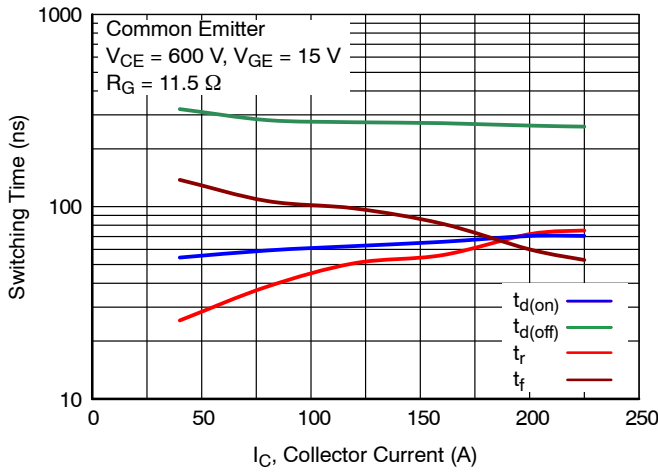


Figure 13. Switching Time vs. Collector Current ( $T_J = 175^\circ\text{C}$ )

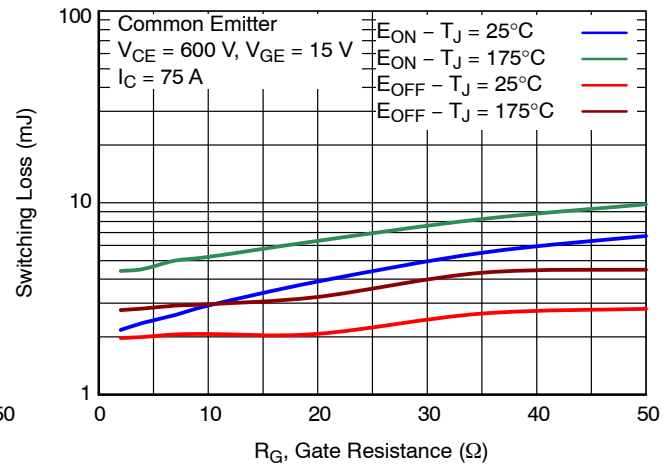


Figure 14. Switching Loss vs. Gate Resistance

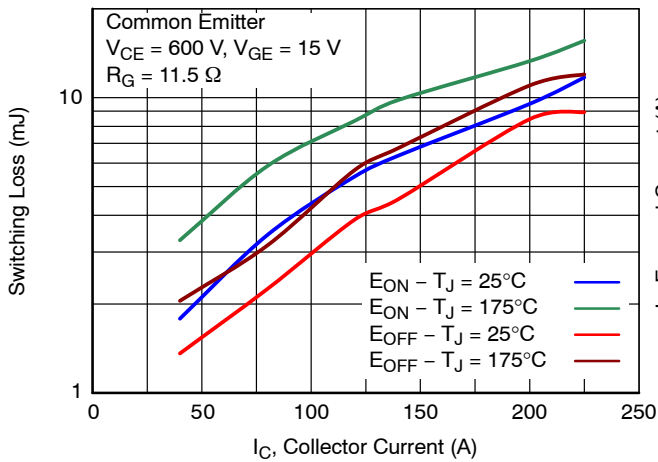


Figure 15. Switching Loss vs. Collector Current

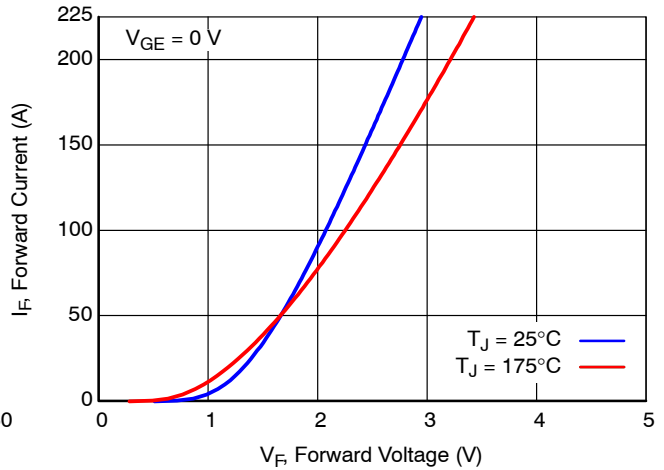


Figure 16. Diode Forward Characteristics

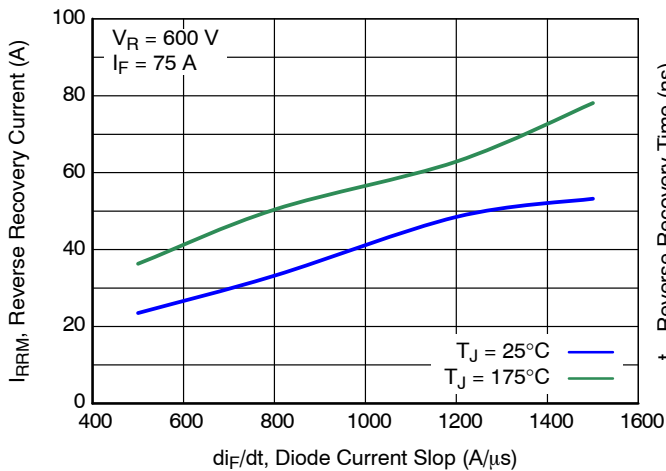


Figure 17. Diode Reverse Recovery Current

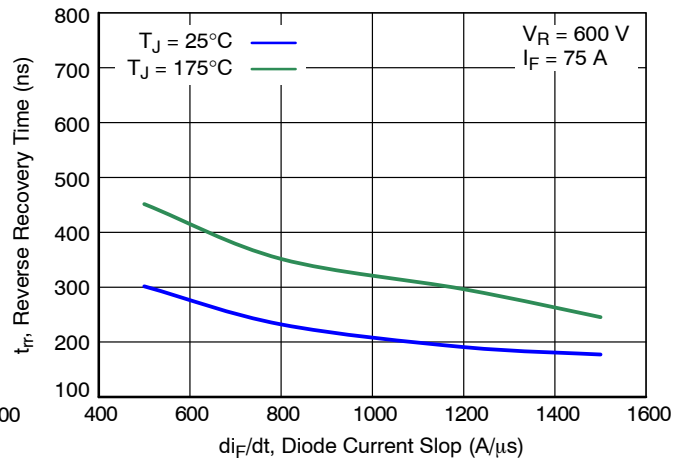


Figure 18. Diode Reverse Recovery Time

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## TYPICAL CHARACTERISTICS

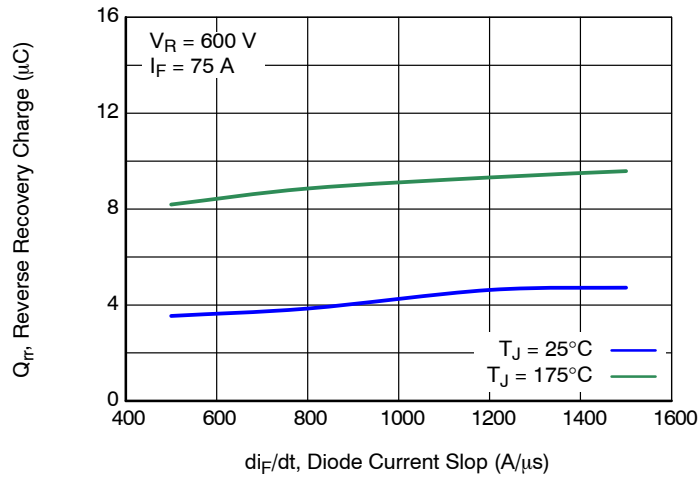


Figure 19. Diode Stored Charge

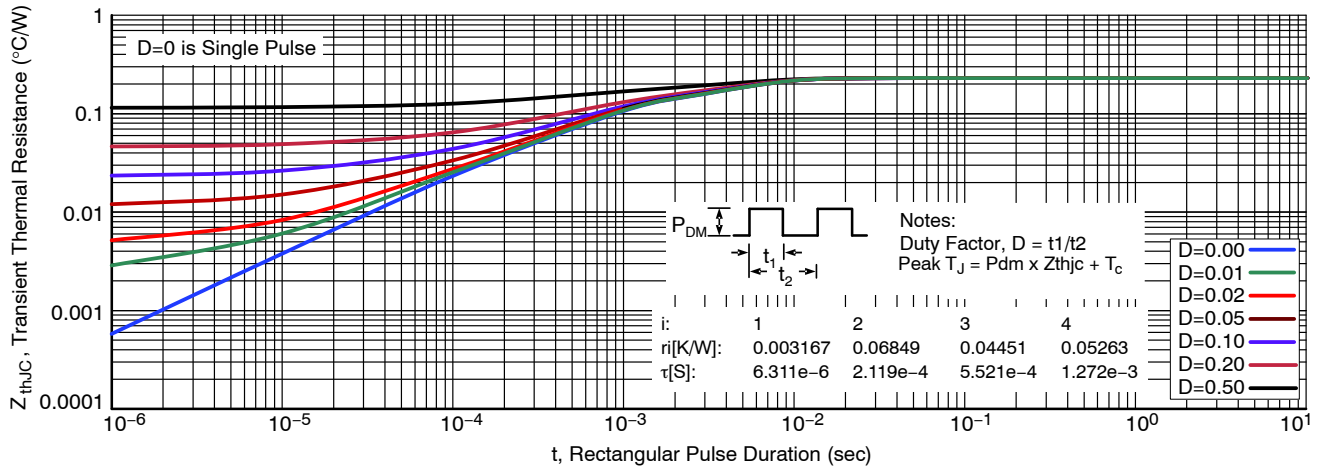


Figure 20. Max Transient Thermal Impedance of IGBT

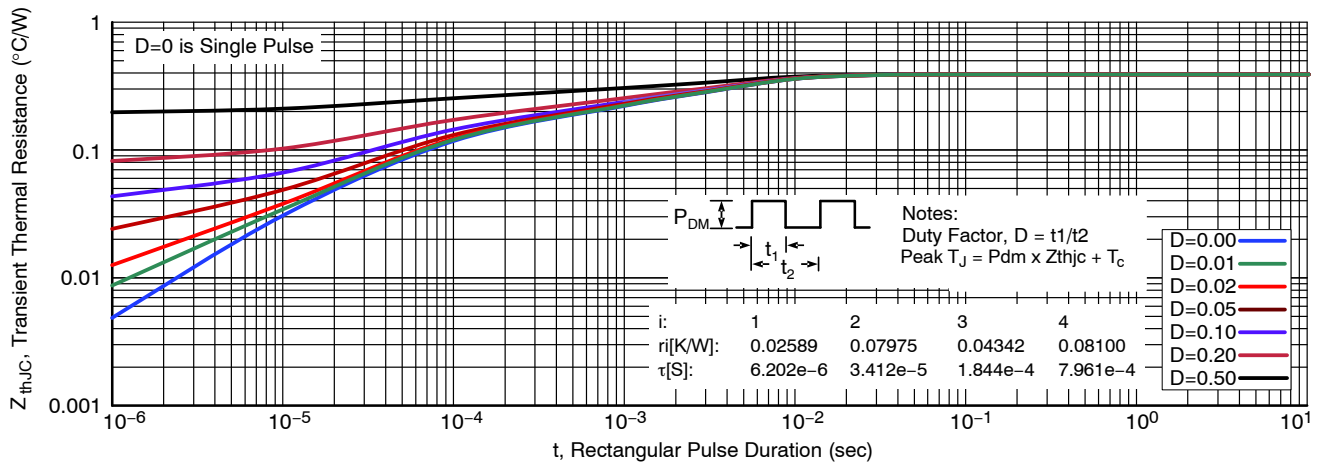
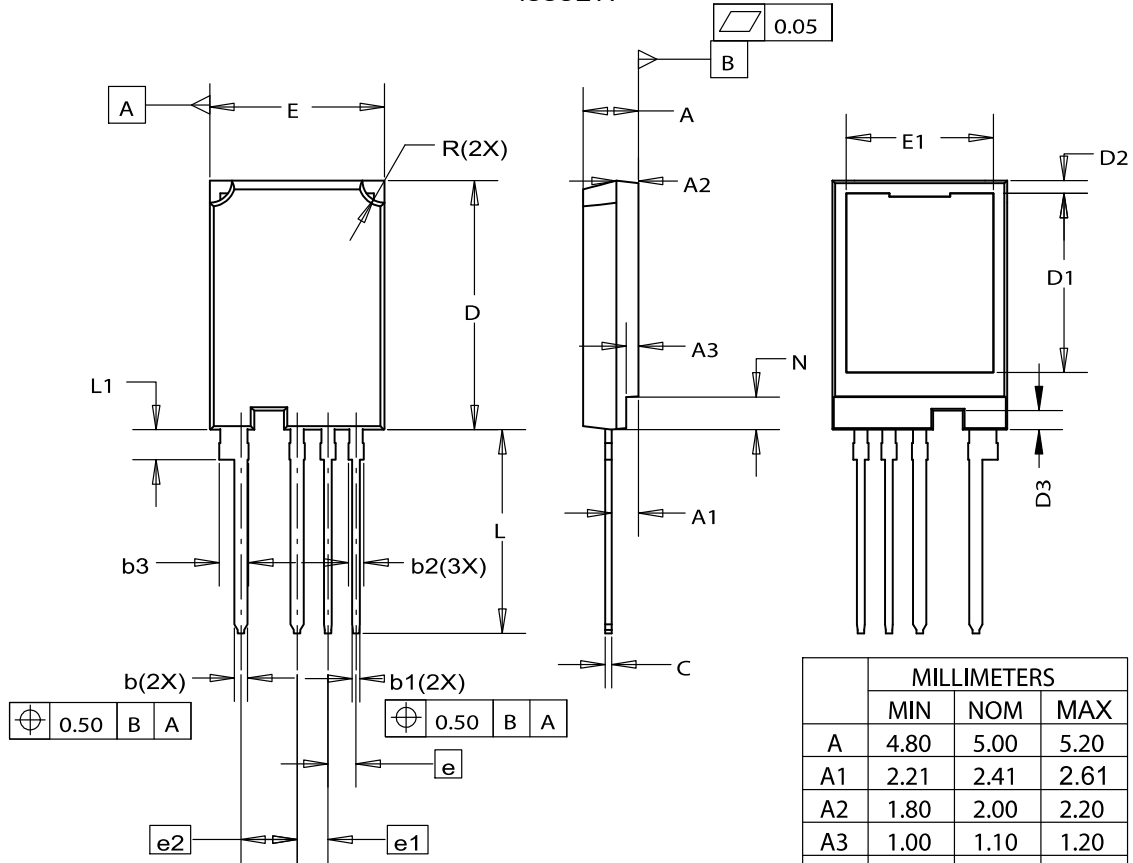


Figure 21. Max Transient Thermal Impedance of Diode

# FGY4L75T120SWD

## PACKAGE DIMENSIONS

TO-247-PLUS-4L 15.80x22.54x5.00, 2.54P  
CASE 340BW  
ISSUE A



### NOTES:

- A. NO INDUSTRY STANDARDS APPLIES TO THIS PACKAGE.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
A3	1.00	1.10	1.20
b	1.07	1.20	1.33
b1	0.57	0.70	0.83
b2	1.20	1.40	1.60
b3	2.47	2.67	2.87
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.20	16.40
D2	0.96	1.16	1.36
D3	1.52	1.72	1.92
e	2.54BSC		
e1	2.79BSC		
e2	5.08BSC		
E	15.60	15.80	16.00
E1	13.10	13.30	13.50
L	18.12	18.42	18.72
L1	2.52	2.72	2.92
R	1.90	2.00	2.10
N	2.75	2.95	3.15



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